## MBR2535CTL

## SWITCHMODE <sup>™</sup> Power Rectifier

#### Features and Benefits

- Low Forward Voltage
- Low Power Loss/High Efficiency
- High Surge Capacity
- 150°C Operating Junction Temperature
- 25 A Total (12.5 A Per Diode Leg)
- Pb-Free Packages are Available\*

#### Applications

- Power Supply Output Rectification
- Power Management
- Instrumentation

#### **Mechanical Characteristics**

- Case: Epoxy, Molded
- Epoxy Meets UL 94, V-0 @ 0.125 in
- Weight: 1.9 Grams (Approximately)
- Finish: All External Surfaces Corrosion Resistant and Terminal Leads are Readily Solderable
- Lead Temperatures for Soldering Purposes: 260°C Max. for 10 Seconds
- ESD Rating: Human Body Model 3B Machine Model C

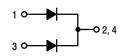
\*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

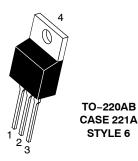


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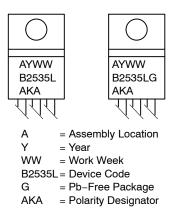
http://onsemi.com

### SCHOTTKY BARRIER RECTIFIER 25 AMPERES, 35 VOLTS





#### MARKING DIAGRAMS



#### **ORDERING INFORMATION**

Device	Package	Shipping
MBR2535CTL	TO-220	50 Units/Rail
MBR2535CTLG	TO-220 (Pb-Free)	50 Units/Rail

BDTIC.com/

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#### MAXIMUM RATINGS (Per Leg)

Rating	Symbol	Value	Unit
Peak Repetitive Reverse Voltage Working Peak Reverse Voltage DC Blocking Voltage	V <sub>RRM</sub> V <sub>RWM</sub> V <sub>R</sub>	35	V
Average Rectified Forward Current $(T_C = 142^{\circ}C \text{ per Diode})$ $(T_C = 142^{\circ}C \text{ per Device})$	I <sub>F(AV)</sub>	12.5 25	A
Peak Repetitive Forward Current, per Leg (Sq Wave, 20 kHz, T <sub>C</sub> = 139°C)	I <sub>FRM</sub>	25	А
Non-Repetitive Peak Surge Current (Surge Applied at Rated Load Conditions, Halfwave, Single Phase, 60 Hz)	I <sub>FSM</sub>	150	A
Peak Repetitive Reverse Surge Current (2.0 μs, 1.0 kHz)	I <sub>RRM</sub>	1.0	Α
Storage Temperature Range	T <sub>stg</sub>	-65 to +150	°C
Operating Junction Temperature (Note 1)	TJ	-65 to +150	°C
Voltage Rate of Change (Rated V <sub>R</sub> )	dv/dt	10,000	V/μs
Controlled Avalanche Energy	W <sub>aval</sub>	20	mJ

Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.

1. The heat generated must be less than the thermal conductivity from Junction-to-Ambient:  $dP_D/dT_J < 1/R_{\theta JA}$ .

#### THERMAL CHARACTERISTICS

Characteristic	Conditions	Symbol	Max	Unit
Maximum Thermal Resistance, Junction-to-Case	Min. Pad	$R_{\theta JC}$	2.0	°C/W
Maximum Thermal Resistance, Junction-to-Ambient	Min. Pad	$R_{\theta JA}$	75.0	

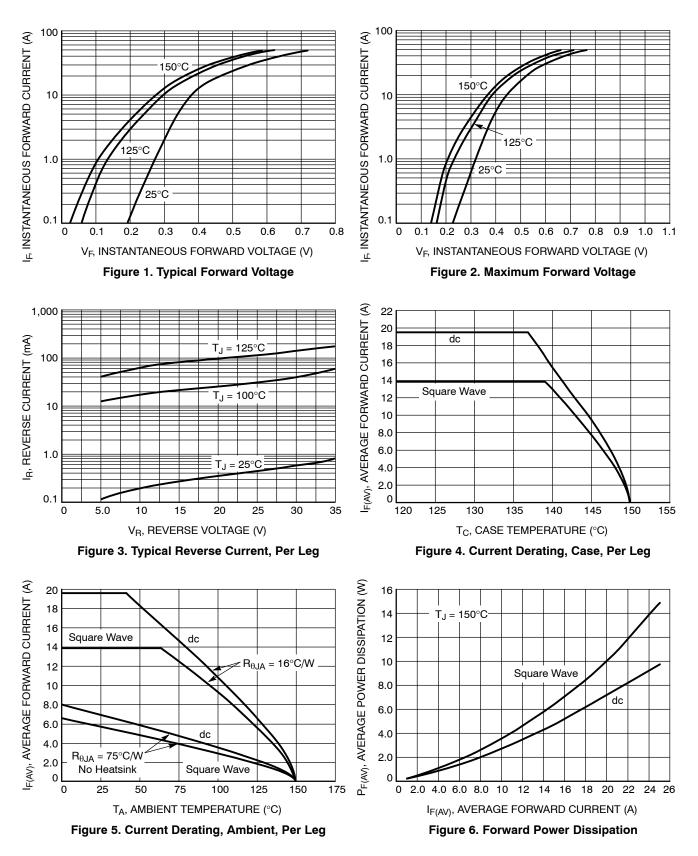
#### **ELECTRICAL CHARACTERISTICS**

Characteristic	Symbol	Min	Typical	Max	Unit
Instantaneous Forward Voltage (Note 2) ( $i_F = 25 \text{ Amps}, T_j = 25^{\circ}\text{C}$ ) ( $i_F = 12.5 \text{ Amps}, T_j = 25^{\circ}\text{C}$ ) ( $i_F = 12.5 \text{ Amps}, T_j = 125^{\circ}\text{C}$ )	v <sub>F</sub>	- - -	0.51 0.41 0.33	0.55 0.47 0.41	V
Instantaneous Reverse Current (Note 2) (Rated dc Voltage, Tj = 25°C) (Rated dc Voltage, Tj = 125°C)	İR		0.8 300	5.0 500	mA

2. Pulse Test: Pulse Width = 300  $\mu s,$  Duty Cycle  $\leq$  2.0%.

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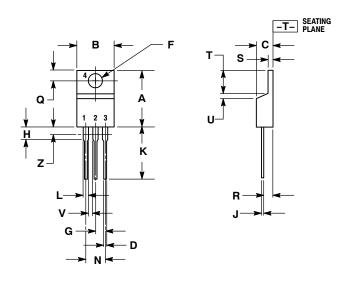
#### MBR2535CTL



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#### PACKAGE DIMENSIONS

TO-220 CASE 221A-09 ISSUE AF



	INC	HES	MILLIMETERS		
DIM	MIN	MAX	MIN	MAX	
Α	0.570	0.620	14.48	15.75	
В	0.380	0.405	9.66	10.28	
С	0.160	0.190	4.07	4.82	
D	0.025	0.035	0.64	0.88	
F	0.142	0.161	3.61	4.09	
G	0.095	0.105	2.42	2.66	
Н	0.110	0.155	2.80	3.93	
J	0.014	0.025	0.36	0.64	
Κ	0.500	0.562	12.70	14.27	
L	0.045	0.060	1.15	1.52	
Ν	0.190	0.210	4.83	5.33	
Q	0.100	0.120	2.54	3.04	
R	0.080	0.110	2.04	2.79	
S	0.045	0.055	1.15	1.39	
Т	0.235	0.255	5.97	6.47	
U	0.000	0.050	0.00	1.27	
۷	0.045		1.15		
Z		0.080		2.04	
style Pin	1. ANO	HODE			

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